

ISC Silicon PNP Power Transistor

2SB689

DESCRIPTION

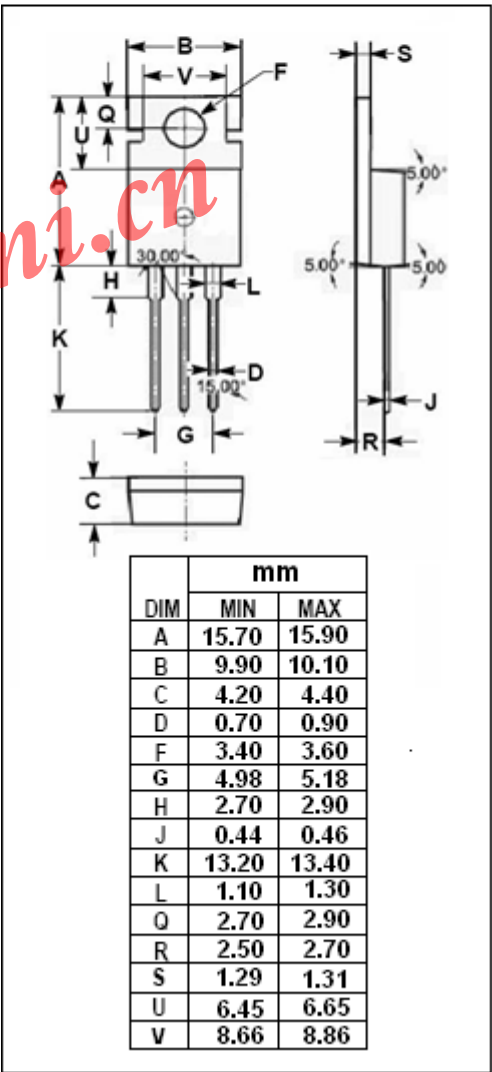
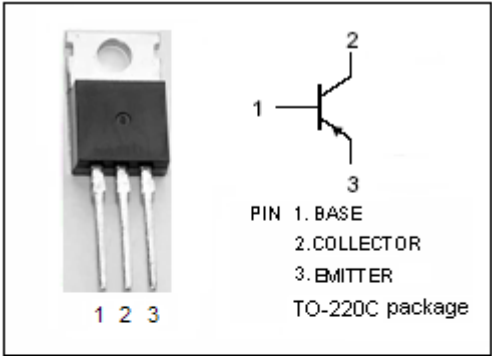
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -100V(\text{Min})$
- High Power Dissipation
- Wide Area of Safe Operation

APPLICATIONS

- Designed for low frequency power amplifier and TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS($T_a=25^{\circ}\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-100	V
V_{CEO}	Collector-Emitter Voltage	-100	V
V_{EBO}	Emitter-Base Voltage	-4	V
I_C	Collector Current-Continuous	-4	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Total Power Dissipation @ $T_a=25^{\circ}\text{C}$	1.8	W
	Total Power Dissipation @ $T_c=25^{\circ}\text{C}$	40	
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature Range	-45~150	$^{\circ}\text{C}$



ISC Silicon PNP Power Transistor**2SB689****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -10mA; R _{BE} = ∞	-100			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -1mA; I _C = 0	-4			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -1A; I _B = -0.1A			-1.0	V
I _{CEO}	Collector Cutoff Current	V _{CE} = -80V; R _{BE} = ∞			-100	μ A
I _{EBO}	Emitter Cutoff Current	V _{EB} = -3.5V; I _C = 0			-50	μ A
h _{FE-1}	DC Current Gain	I _C = -0.5A; V _{CE} = -4V	50		250	
h _{FE-2}	DC Current Gain	I _C = -50mA; V _{CE} = -4V	25		350	